

Silicon PNP Power Transistors

2SB1568

DESCRIPTION

- With TO-220F package
- Complement to type 2SD2399
- High DC current gain.
- Low saturation voltage.
- DARLINGTON

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

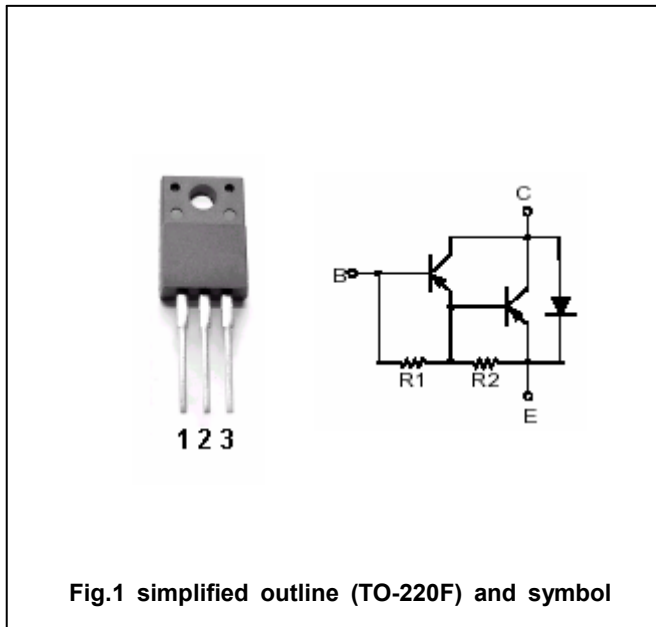


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-80	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-4	A
I _{CM}	Collector current-peak		-6	A
P _C	Collector dissipation	T _C =25°C	30	W
			2	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA; I _B =0	-80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-50μA; I _E =0	-80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA; I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-4mA		-1.0	-3.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V; I _E =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-3.0	mA
h _{FE}	DC current gain	I _C =-2A; V _{CE} =-3V	1000		10000	
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		35		pF
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-5V; f=10MHz		12		MHz

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PACKAGE OUTLINE

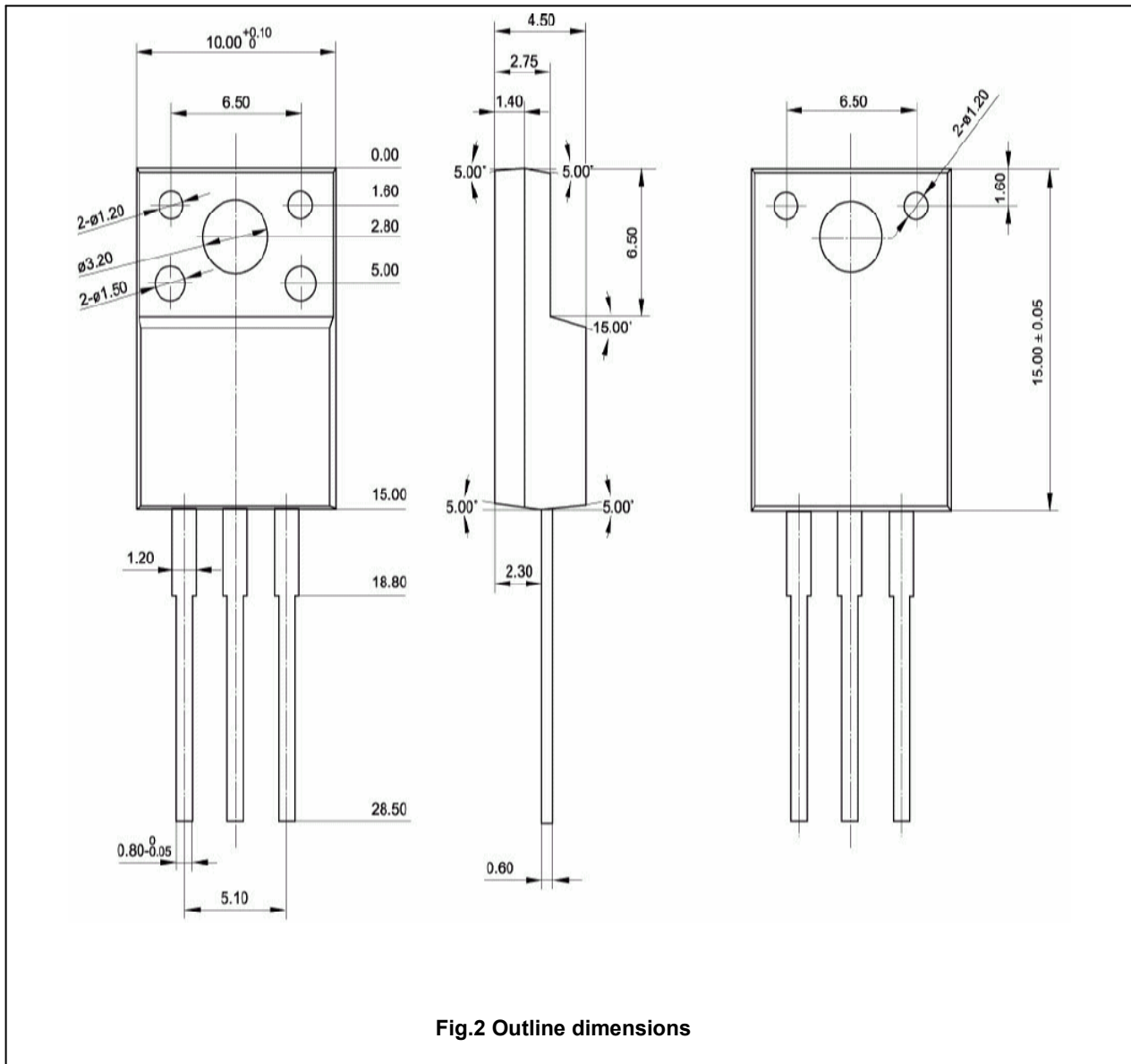


Fig.2 Outline dimensions